PAC2332EH

N-Ch and P-Ch Fast Switching MOSFET

V_{DS}=20V, I_D=1.2A, $RDS_{(ON)}$=320mΩ

V_{DS}=-20V, I_D=-1.0A, $RDS_{(ON)}$=580mΩ

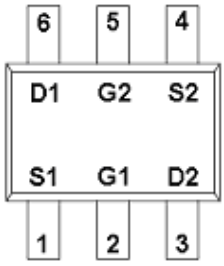
➢ General Description

This PAC2332EH N&P Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent Rds(On) performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➢ Feature

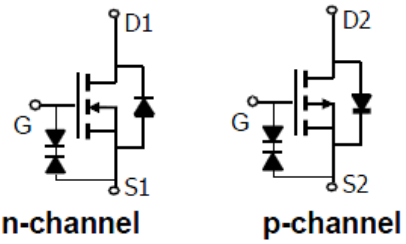
- ●Low Offset (Error) Voltage
- ●Low-Voltage Operation
- ●High-Speed Circuits
- ●ESD Protection
- ●Low Battery Voltage Operation
- ●SOT-363 package design

➢ SOT-363



➢ Application

- ●Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- ●Battery Operated Systems
- ●Load/Power Switching Smart Phones, Pagers
- ●PA Switch
- ●Level Switch



n-channel p-channel

➢ Absolute Maximum Ratings

Parameter		Symbol	Rating		Unit
			N-Channel	P-Channel	
Drain-Source Voltage		V_{DSS}	20	-20	V
Gate –Source Voltage		V_{GSS}	±12	±12	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	1.2	-1.0	A
	T_A=70℃		0.9	-0.7	
Pulsed Drain Current		I_{DM}	4	-3	A
Continuous Source Current(Diode Conduction)		I_S	0.6	-0.6	A
Power Dissipation	T_A=25℃	P_D	0.3		W
	T_A=70℃		0.2		
Operating Junction Temperature		T_J	-55/150		℃
Storage Temperature Range		T_{STG}	-55/150		℃

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➢ N-Channel Electrical Characteristics (TJ=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	0.3		1.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±1	mA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=16V,V_{GS}=0V			1	uA
		V_{DS}=16V,V_{GS}=0V T_J=85℃			5	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧5V,V_{GS}=4.5V	1.2			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=4.5V,I_D=0.7A		230	320	mΩ
		V_{GS}=2.5V,I_D=0.6A		280	420	
		V_{GS}=1.8V,I_D=0.5A		400	580	
Forward Transconductance	g_{FS}	V_{DS}=10V,I_D=1.0A		1		S
Diode Forward Voltage	V_{SD}	I_S=1.0A,V_{GS}=0V		0.65	1.5	V
Dynamic						
Input Capacitance	C_{iss}	V_{DS}=10V,V_{GS}=0V f=1MHz		70		pF
Output Capacitance	C_{oss}			20		
Reverse Transfer Capacitance	C_{rss}			8		
Total Gate Charge	Q_g	V_{DS}=10V,V_{GS}=4.5V I_D≡1.2A		1.06	1.38	nC
Gate-Source Charge	Q_{gs}			0.18		
Gate-Drain Charge	Q_{gd}			0.32		
Turn-On Time	$t_{d(on)}$	V_{DD}=10V,R_L=20Ω I_D≡1.2A,V_{GEN}=4.5V R_G=1Ω		18	26	ns
	t_r			20	28	
Turn-Off Time	$t_{d(off)}$			70	110	
	t_f			25	40	

N-Ch and P-Ch Fast Switching MOSFET

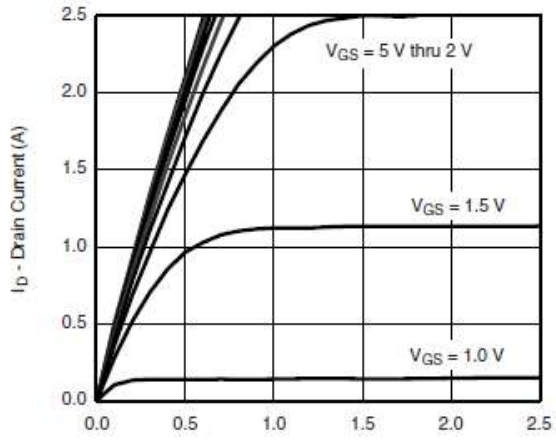
V_{DS}=20V, I_D=1.2A, $RDS_{(ON)}$=320mΩ

V_{DS}=-20V, I_D=-1.0A, $RDS_{(ON)}$=580mΩ

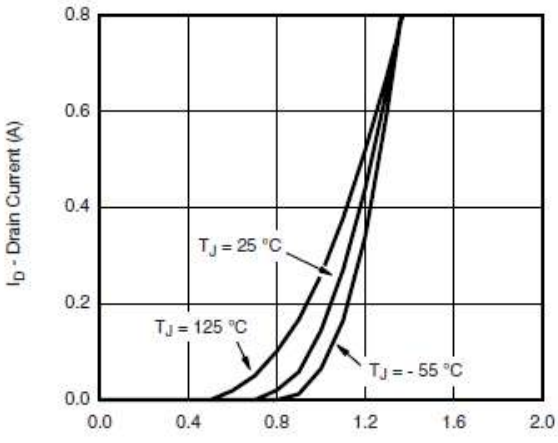
➢ P-Channel Electrical Characteristics (TJ=25° C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250uA	-0.3		-1.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±1	mA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-16V,V_{GS}=0V			-1	uA
		V_{DS}=-16V,V_{GS}=0V T_J=85℃			-5	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧5V,V_{GS}=4.5V	0.7			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-4.5V,I_D=-0.6A		380	580	mΩ
		V_{GS}=-2.5V,I_D=-0.5A		520	780	
		V_{GS}=-1.8V,I_D=-0.4A		690	980	
Forward Transconductance	g_{FS}	V_{DS}=-10V,I_D=-0.4A		1		S
Diode Forward Voltage	V_{SD}	I_S=-0.15A,V_{GS}=0V		0.65	1.5	V
Dynamic						
Input Capacitance	C_{iss}	V_{DS}=-10V,V_{GS}=0V f=1MHz		70	100	pF
Output Capacitance	C_{oss}			20		
Reverse Transfer Capacitance	C_{rss}			10		
Total Gate Charge	Q_g	V_{DS}=-10V,V_{GS}=-4.5V I_D≡-0.25A		1.0	1.3	nC
Gate-Source Charge	Q_{gs}			0.1		
Gate-Drain Charge	Q_{gd}			0.3		
Turn-On Time	$t_{d(on)}$	V_{DD}=-10V,R_L=30Ω I_D≡-0.2A,V_{GEN}=-4.5V R_G=10Ω		10	15	ns
	t_r			10	15	
Turn-Off Time	$t_{d(off)}$			40	60	
	t_f			30	50	

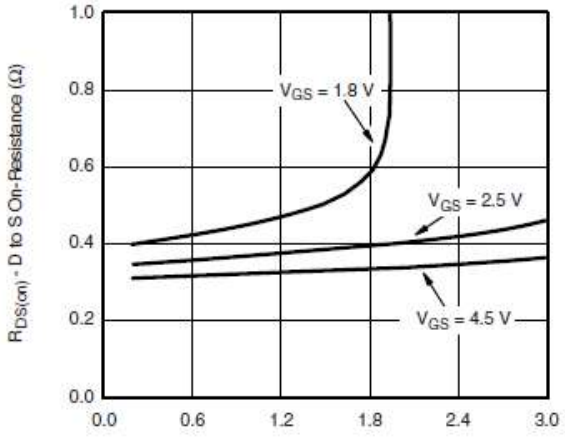
➢ Typical Characteristics(N-Channel)



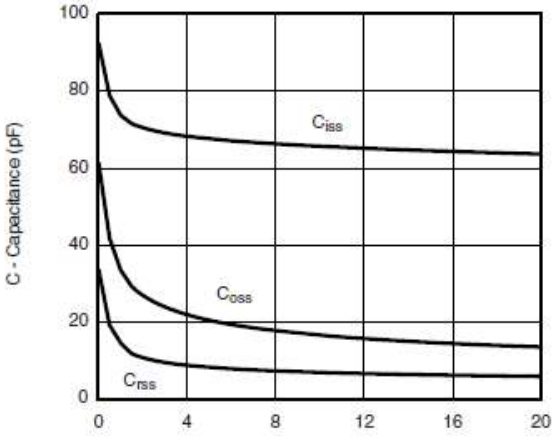
Output Characteristics



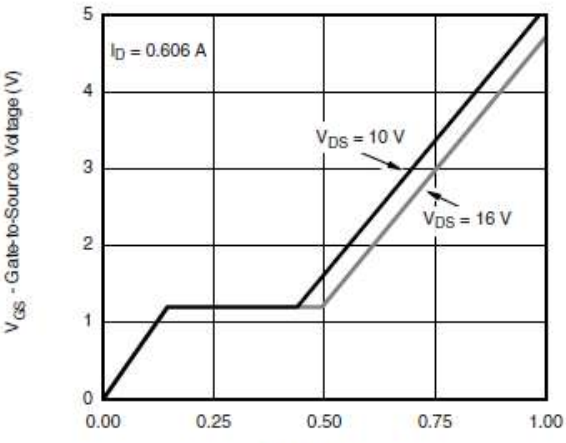
Transfer Characteristics



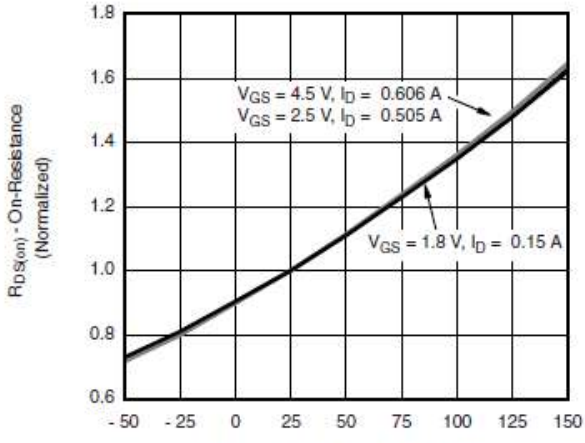
On-Resistance vs. Drain Current



Capacitance

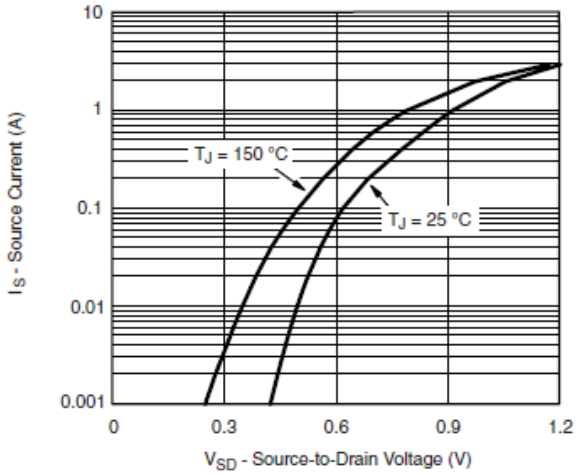


Gate Charge

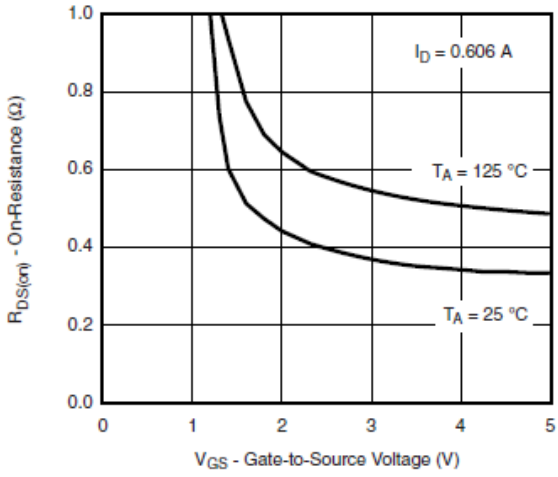


On-Resistance vs. Junction Temperature

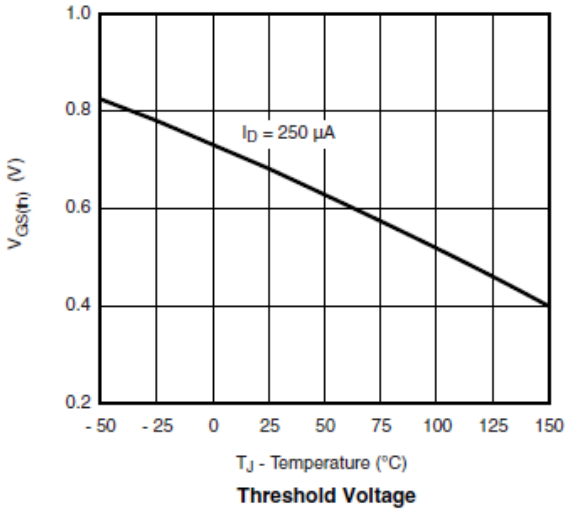
➢ Typical Characteristics(N-Channel)



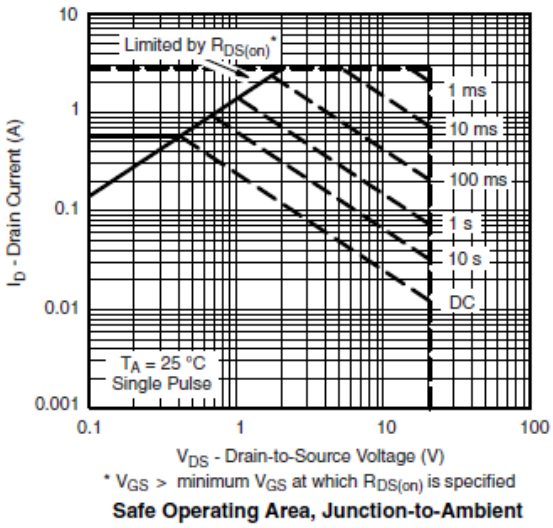
Source-Drain Diode Forward Voltage



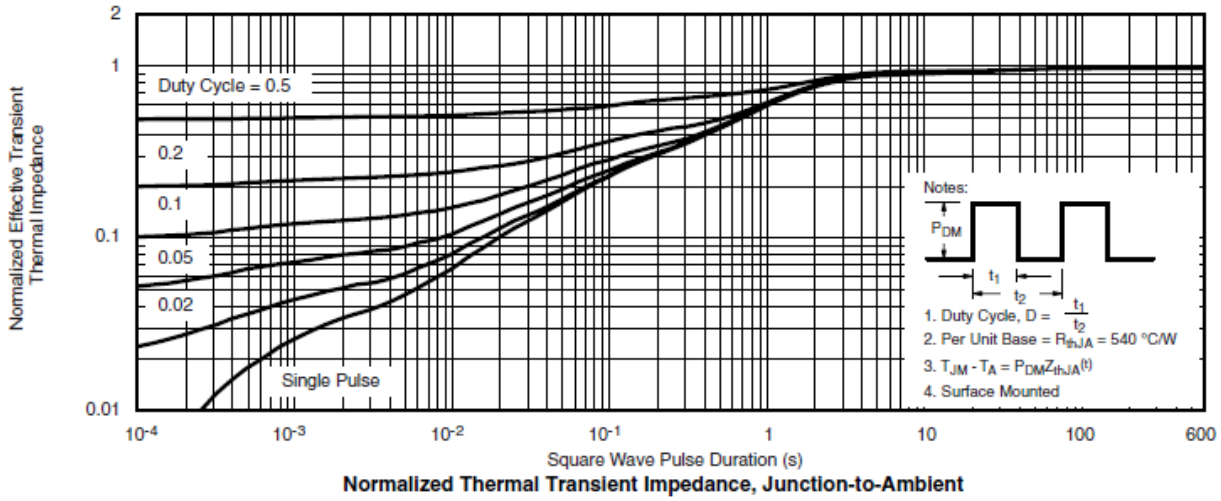
$R_{DS(on)}$ vs. V_{GS} vs Temperature



Threshold Voltage

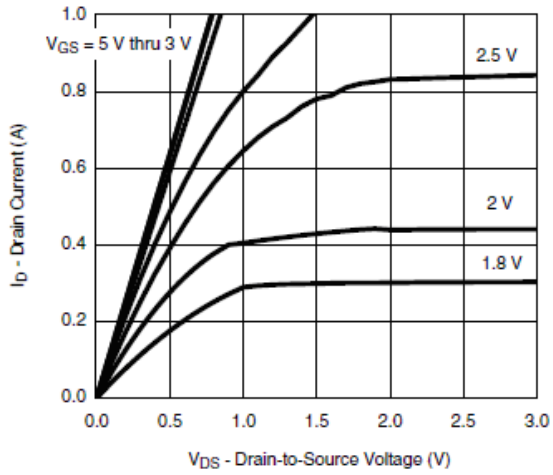


Safe Operating Area, Junction-to-Ambient

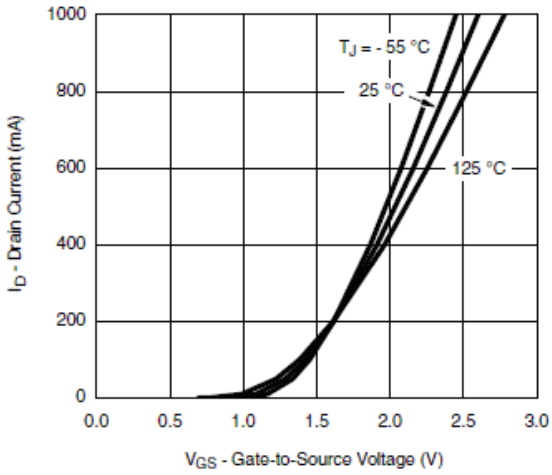


Normalized Thermal Transient Impedance, Junction-to-Ambient

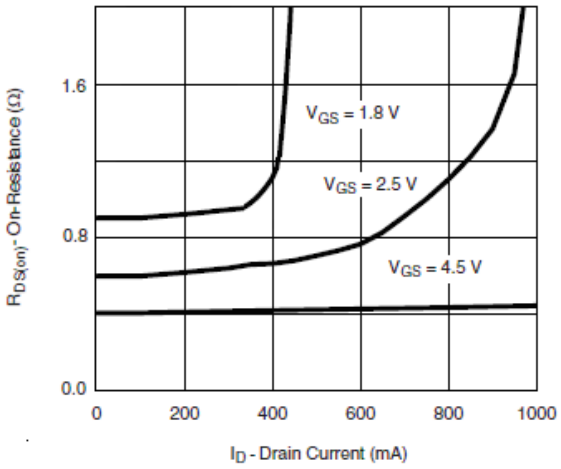
➢ Typical Characteristics(P-Channel)



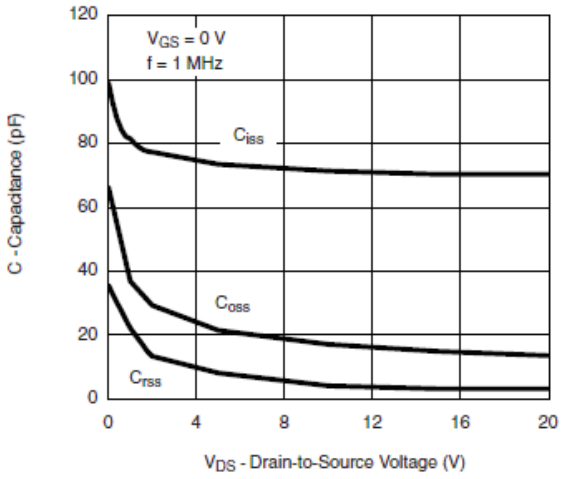
Output Characteristics



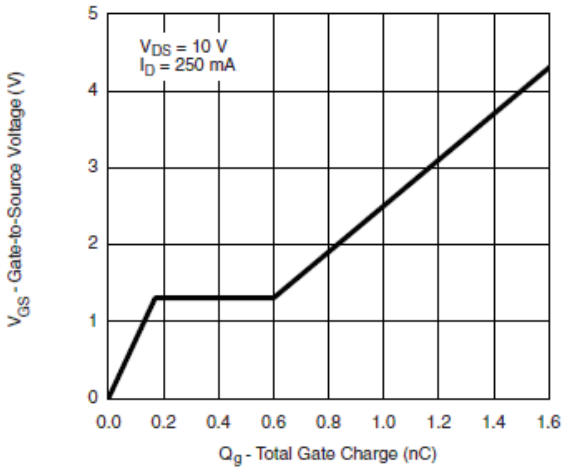
Transfer Characteristics



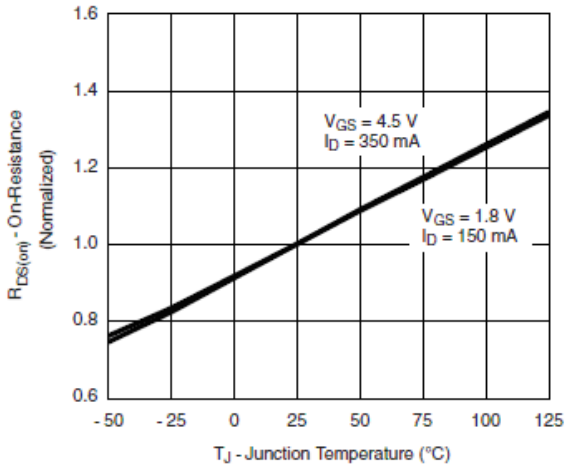
On-Resistance vs. Drain Current



Capacitance

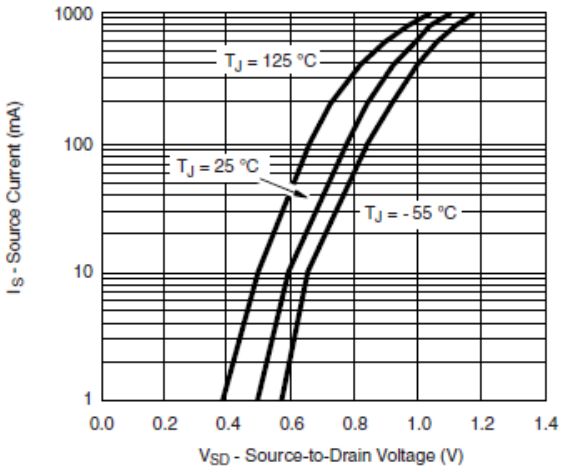


Gate Charge

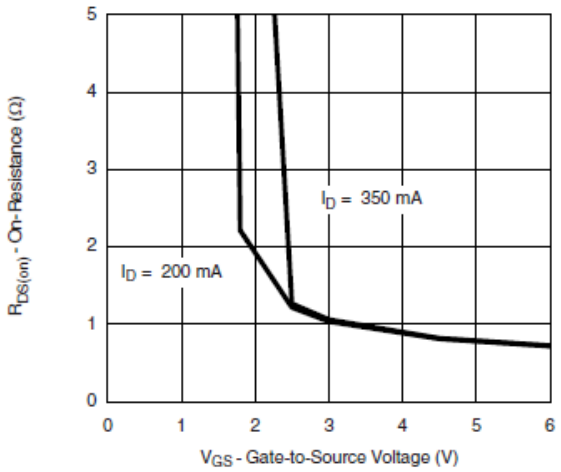


On-Resistance vs. Junction Temperature

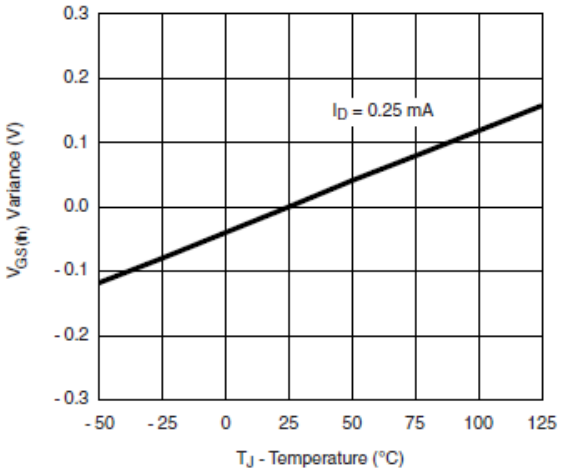
➢ Typical Characteristics(P-Channel)



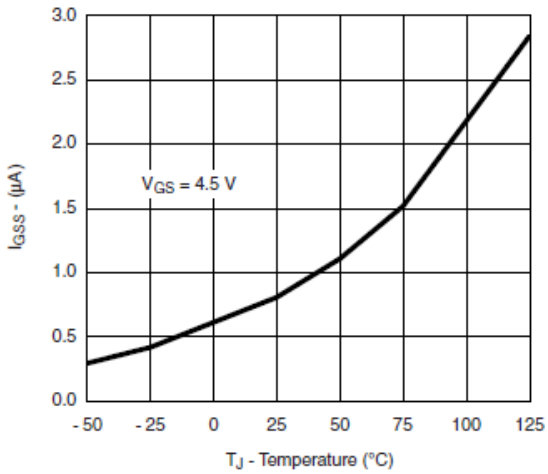
Source-Drain Diode Forward Voltage



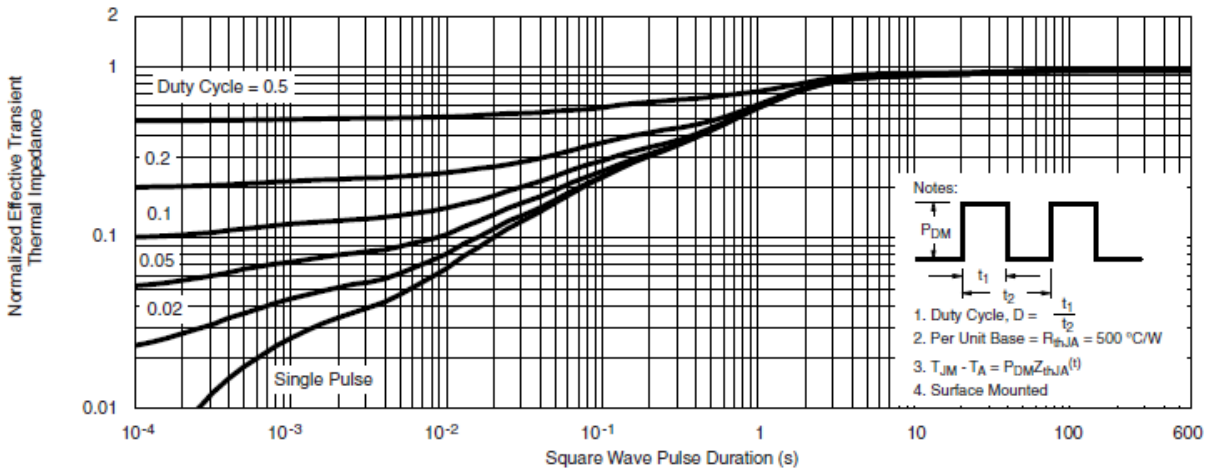
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage Variance vs. Temperature

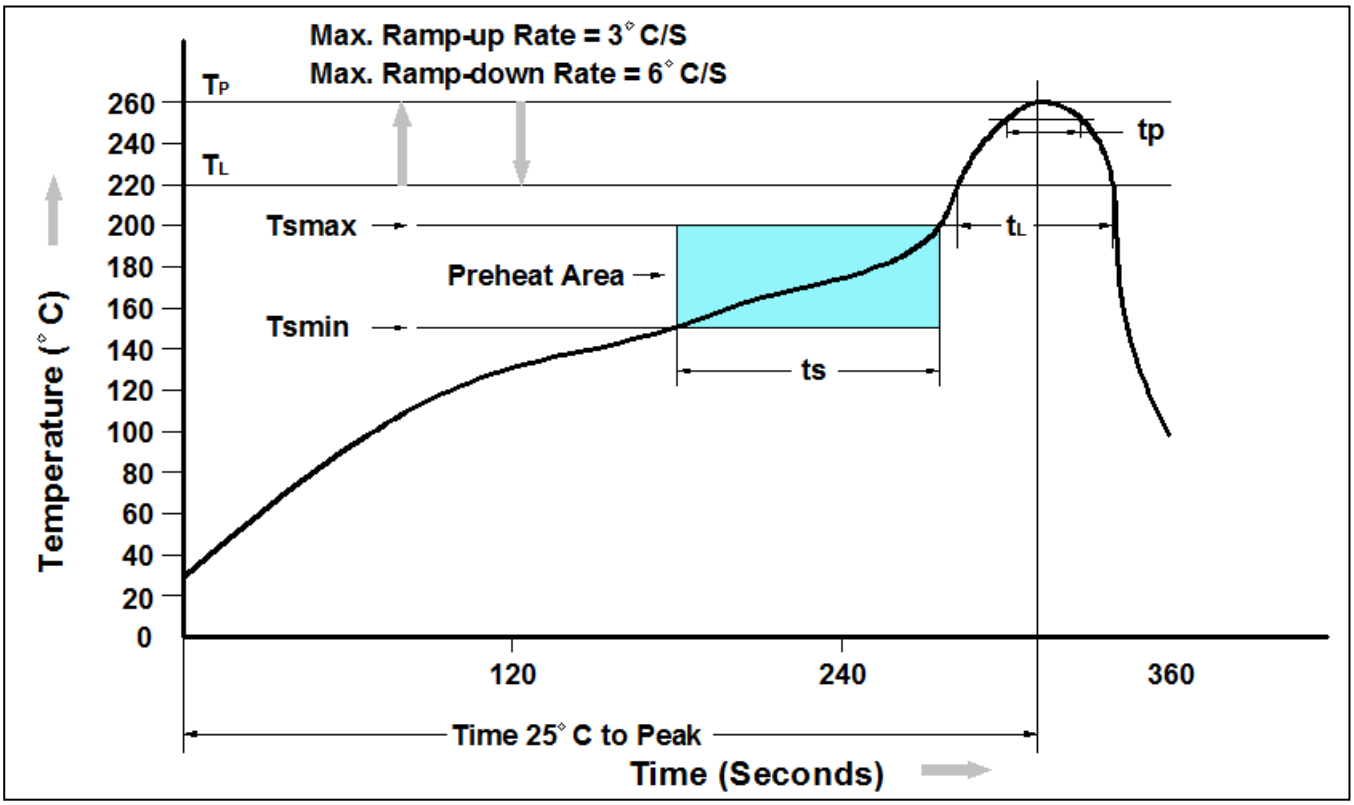


I_{GSS} vs. Temperature



Normalized Thermal Transient Impedance, Junction-to-Ambient

➢ Recommand IR Reflow Soldering Thermal Profile

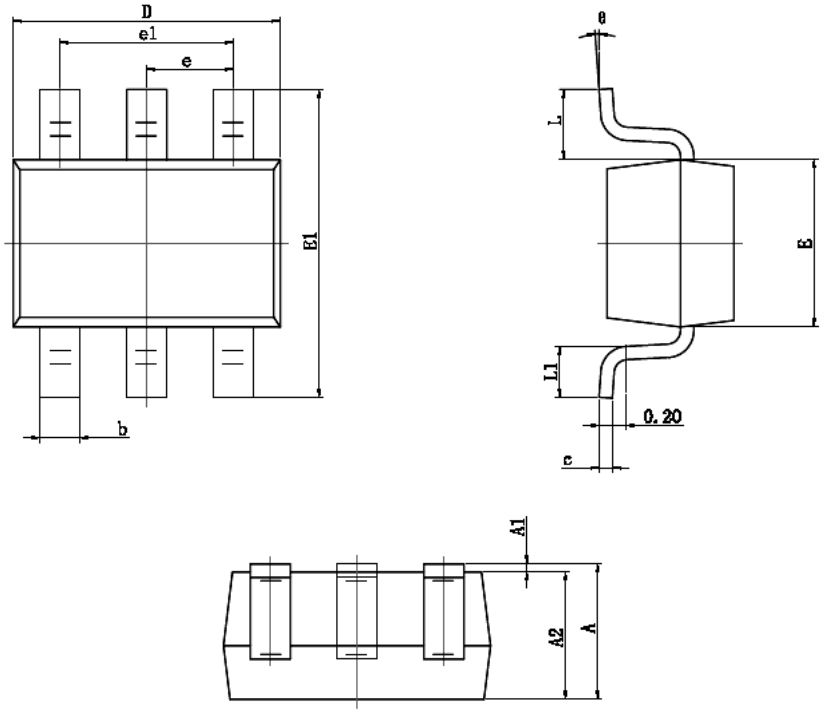


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Average Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (tP) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➢ Ordering Information

Part Number	Description	Quantity
PAC2332EH	SOT-363 Reel	3000 pcs

➢ Package Information (SOT-363)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

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